

RoHS

COMPLIANT HALOGEN

FREE Available

Vishay Siliconix

N-Channel 250-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	Rr_{DS(on)} (Ω)	I _D (A)			
250	0.155 at V _{GS} = 10 V	3.0			
	0.162 at V _{GS} = 6.0 V	2.9			

8 D

7 D

6 D

5 D

Si4434DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

SO-8

Top View
Ordering Information: Si4434DY-T1-E3 (Lead (Pb)-free)

S

S 2

s

G 4

1

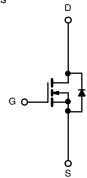
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FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- PWM-Optimized TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Avalanche Tested

APPLICATIONS

- Primary Side Switch In:
 - Telecom Power Supplies
 - Distributed Power Architectures
 - Miniature Power Modules



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	250		V	
Gate-Source Voltage		V _{GS}	± 20			
	T _A = 25 °C	– I _D	3.0	2.1		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		2.4	1.7		
Pulsed Drain Current		I _{DM}	30		А	
Continuous Source Current (Diode Conduction) ^a		ا _S	2.6	1.3		
Avalanche Current	L = 0.1 mH	I _{AS}	13			
Single Pulse Avalanche Energy		E _{AS}	8.4		mJ	
	T _A = 25 °C	Pn	3.1	1.56	W	
Maximum Power Dissipation ^a	T _A = 70 °C	'D	2.0	1.0	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	R _{thJA}	33	40	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		65	80		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	2.0		4.0	V	
Gate-Body Leakage	I _{GSS}				± 100	nA	
Zava Cata Valtaga Drain Current	1	V _{DS} = 250 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	IDSS	V_{DS} = 250 V, V_{GS} = 0 V, T_{J} = 55 °C			15	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10$ V, $V_{GS} = 10$ V	20			А	
	D	V _{GS} = 10 V, I _D = 3.0 A		0.129	0.155	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6.0 \text{ V}, \text{ I}_{D} = 2.9 \text{ A}$		0.131	0.162	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 3.0 A		14		S	
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = 2.8 A, $V_{\rm GS}$ = 0 V		0.75	1.2	V	
Dynamic ^b			•	•			
Total Gate Charge	Qg			34	50		
Gate-Source Charge	Q _{gs}	V_{DS} = 100 V, V_{GS} = 10 V, I_{D} = 3.0 A		6.8		nC	
Gate-Drain Charge	Q _{gd}			10.5			
Gate Resistance	R _g		0.6	1.2	1.8	Ω	
Turn-On Delay Time	t _{d(on)}			16	25		
Rise Time	t _r	V_{DD} = 100 V, R_L = 25 Ω		23	35		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_{\text{D}}\cong$ 4.0 A, V_{GEN} = 10 V, R_{g} = 6 Ω		47	70	ns	
Fall Time	t _f			19	30		
Source-Drain Reverse Recovery Time	t _{rr}	t _{rr} I _F = 2.8 A, dI/dt = 100 A/μs		100	150		

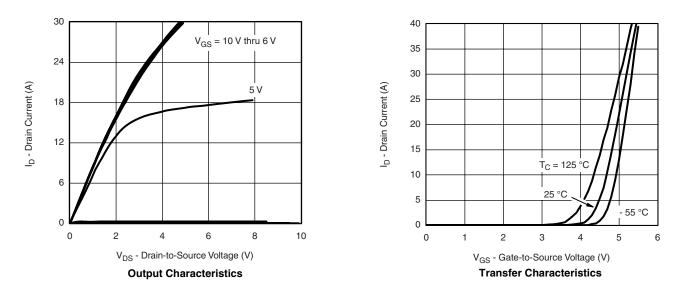
Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

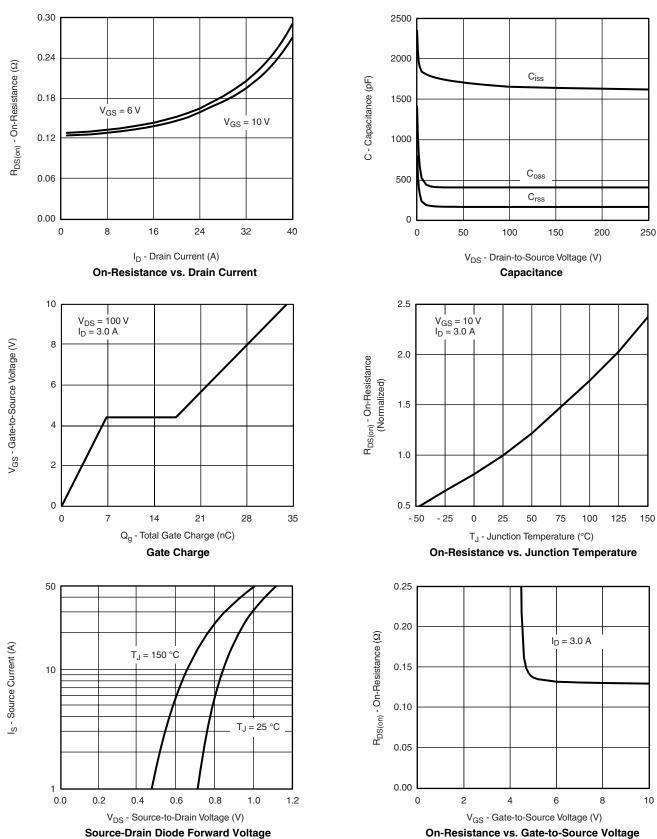
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Si4434DY Vishay Siliconix

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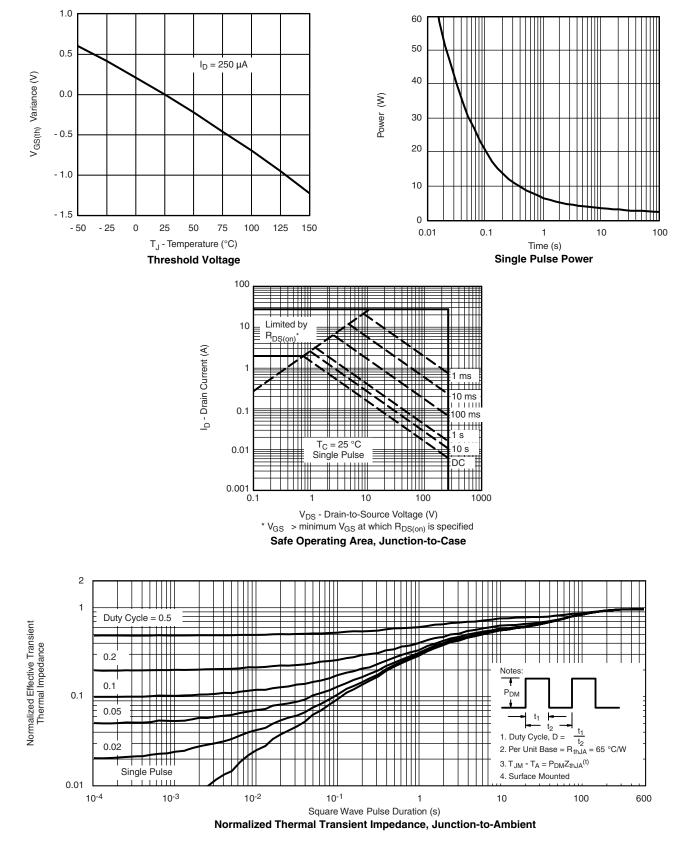
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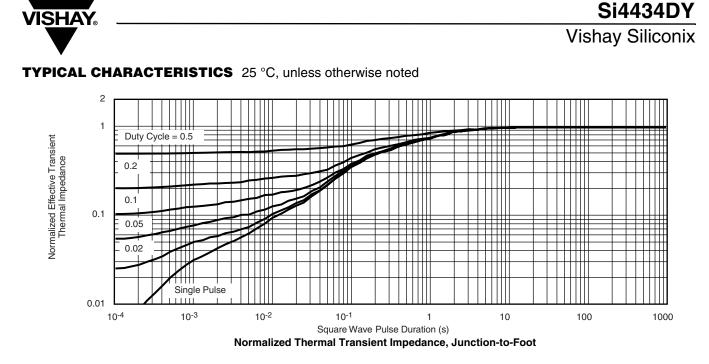
Document Number: 72562 S09-0322-Rev. D, 02-Mar-09

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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72562.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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